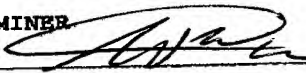


Sheet 1 of 1										Atty. Docket No. 3905		Serial No.: 09/519,408		
FIFTH LIST OF REFERENCES CITED BY APPLICANT (REVISED FORM PTO-1449) DATED: <u>December 27, 2002</u>										Applicant: Takao NAKAMURA et al.				
										U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02				Art Unit: 2814
U. S. PATENT DOCUMENTS														
*EXAMINER INITIAL		DOCUMENT NO.							DATE	NAME	Cl.	Sub- Cl.	File Date	
WBL	AC2	5	4	1	1	7	7	2	05/1995	Cheung	-	-	-	
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													Yes	No
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OTHER DOCUMENTS														
EXAMINER 										DATE CONSIDERED 1/24/03				
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Sheet 1 of 2Atty. Docket
No. 3905Serial No.:
09/519,408**FOURTH
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APPLICANT**

(REVISED FORM PTO-1449)

DATED: June 18, 2002

Applicant: Takao NAKAMURA et al.

U.S. Filing Date:
March 3, 2000
CPA FILED: 03/18/02Art Unit:
2811

U. S. PATENT DOCUMENTS

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				-	-	-

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WSL	AE	57	0	9	7	6	8	6	06/1982	Japan	-	-	x-Abstract	
	AF	57-	1	0	6	2	4	6	06/1982	Japan <i>Utility Model</i>	-	-	x-Par. Trans.	
	AG	58	1	6	2	0	7	6	09/1983	Japan	-	-	x-Abstract	
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	AL	06	2	8	3	4	3	3	10/1994	Japan	-	-	x-Abstract	
	AM	08	1	0	2	5	4	8	04/1996	Japan	-	-	x-Abstract	
	AN	10	0	1	2	9	2	1	01/1998	Japan	-	-	x-Abstract	
	AO	10	0	7	4	5	8	6	03/1998	Japan	-	-	x-Abstract	
	AP	10	2	0	0	1	6	3	07/1998	Japan	-	-	x-Abstract	
	AQ	10	3	0	8	5	3	4	11/1998	Japan	-	-	x-Abstract	
	AR	11	0	8	7	7	7	2	03/1999	Japan	-	-	x-Abstract	
	AS	11	1	2	1	8	0	4	04/1999	Japan	-	-	x-Abstract	
	AT	2000	1	9	6	1	5	2	07/2000	Japan	-	-	x-Abstract	

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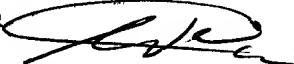
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DATE CONSIDERED

7/29/02

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				Applicant: Takao NAKAMURA et al.			
				U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02		Art Unit: 2811	
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*EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	Cl.	Sub- Cl.	Fil. Date
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WSL	AV	Y. Fan et al.; "Graded band gap ohmic contact to p-ZnSe"; Appl. Phys. Lett. 61 (26), 28 December 1992, 1992 American Institute of Physics, pages 3160 to 3162.					
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	AY	S. J. Pearton et al.; "Ion implantation doping and isolation of GaN", Appl. Phys. Lett. 67 (10), 4. September, 1995, 1995 American Institute of Physics, pages 1435 to 1437.					
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